

Title (en)

HIGH POWER MMIC DEVICES HAVING BYPASSED GATE TRANSISTORS

Title (de)

MMIC-HOCHLEISTUNGSVORRICHTUNGEN MIT BYPASS-GATE-TRANSISTOREN

Title (fr)

DISPOSITIFS MMIC À HAUTE PUISSANCE AYANT DES TRANSISTORS DE GRILLE DÉRIVÉS

Publication

**EP 3619738 A4 20210113 (EN)**

Application

**EP 18795054 A 20180503**

Priority

- US 201715587830 A 20170505
- US 201715608048 A 20170530
- US 2018030863 W 20180503

Abstract (en)

[origin: WO2018204622A1] Monolithic microwave integrated circuits are provided that include a substrate having a transistor and at least one additional circuit formed thereon. The transistor includes a drain contact extending in a first direction, a source contact extending in the first direction in parallel to the drain contact, a gate finger extending in the first direction between the source contact and the drain contact and a gate jumper extending in the first direction. The gate jumper conductively connects to the gate finger at two or more locations that are spaced apart from each other along the first direction.

IPC 8 full level

**H01L 23/482** (2006.01); **H01L 29/40** (2006.01); **H01L 29/423** (2006.01); **H01L 29/43** (2006.01); **H01L 29/739** (2006.01); **H01L 29/778** (2006.01)

CPC (source: CN EP)

**H01L 23/482** (2013.01 - CN EP); **H01L 23/4824** (2013.01 - CN EP); **H01L 25/16** (2013.01 - CN); **H01L 29/402** (2013.01 - CN); **H01L 29/4238** (2013.01 - CN EP); **H01L 29/7786** (2013.01 - CN EP); **H01L 29/402** (2013.01 - EP)

Citation (search report)

- [IAY] US 2013313653 A1 20131128 - BRECH HELMUT [DE]
- [A] JP H01166564 A 19890630 - NEC CORP
- [Y] WO 2016042861 A1 20160324 - SHARP KK [JP]
- See also references of WO 2018204622A1

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

DOCDB simple family (publication)

**WO 2018204622 A1 20181108**; CN 110582846 A 20191217; CN 110582846 B 20230512; CN 116403982 A 20230707; EP 3619738 A1 20200311; EP 3619738 A4 20210113; JP 2020519025 A 20200625; JP 2022002308 A 20220106; JP 2023081974 A 20230613; JP 6929968 B2 20210901; JP 7242777 B2 20230320

DOCDB simple family (application)

**US 2018030863 W 20180503**; CN 201880029743 A 20180503; CN 202310564820 A 20180503; EP 18795054 A 20180503; JP 2019560218 A 20180503; JP 2021131203 A 20210811; JP 2023035192 A 20230308